

LC²MOS Precision Mini-DIP Analog Switch

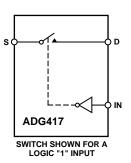
ADG417

FEATURES

44 V Supply Maximum Ratings V_{SS} to V_{DD} Analog Signal Range Low On Resistance (<35 Ω) Ultralow Power Dissipation (<35 μ W) Fast Switching Times t_{ON} (160 ns max) t_{OFF} (100 ns max) Break-Before-Make Switching Action Plug-In Replacement for DG417

APPLICATIONS
Precision Test Equipment
Precision Instrumentation
Battery Powered Systems
Sample Hold Systems

FUNCTIONAL BLOCK DIAGRAM



GENERAL DESCRIPTION

The ADG417 is a monolithic CMOS SPST switch. This switch is designed on an enhanced LC²MOS process that provides low power dissipation yet gives high switching speed, low on resistance and low leakage currents.

The on resistance profile of the ADG417 is very flat over the full analog input range ensuring excellent linearity and low distortion. The part also exhibits high switching speed and high signal bandwidth. CMOS construction ensures ultralow power dissipation making the parts ideally suited for portable and battery powered instruments.

The ADG417 switch, which is turned ON with a logic low on the control input, conducts equally well in both directions when ON and has an input signal range that extends to the supplies. In the OFF condition, signal levels up to the supplies are blocked. The ADG417 exhibits break-before-make switching action for use in multiplexer applications. Inherent in the design is low charge injection for minimum transients when switching the digital input.

PRODUCT HIGHLIGHTS

- Extended Signal Range
 The ADG417 is fabricated on an enhanced LC²MOS process, giving an increased signal range that extends to the supply rails.
- 2. Ultralow Power Dissipation
- 3. Low Ron
- 4. Single Supply Operation
 For applications where the analog signal is unipolar, the ADG417 can be operated from a single rail power supply.
 The part is fully specified with a single +12 V power supply and will remain functional with single supplies as low as +5 V.

ADG417—SPECIFICATIONS

 $\textbf{Dual Supply}^{1} \ \, (\textbf{V}_{DD} = +15 \ \textbf{V} \ \pm \ 10\%, \ \textbf{V}_{SS} = -15 \ \textbf{V} \ \pm \ 10\%, \ \textbf{V}_{L} = +5 \ \textbf{V} \ \pm \ 10\%, \ \textbf{GND} = 0 \ \textbf{V}, \ \textbf{unless otherwise noted})$

	B Version		T Version			
Parameter	+25°C	−40°C to +85°C	+25°C	-55°C to +125°C	Units	Test Conditions/Comments
ANALOG SWITCH						
Analog Signal Range		V_{SS} to V_{DD}		V _{SS} to V _{DD}	V	
$R_{ m ON}$	25	00 DD	25	55 EE	Ω typ	$V_D = \pm 12.5 \text{ V}, I_S = -10 \text{ mA}$
	35	45	35	45	Ω max	$V_{DD} = +13.5 \text{ V}, V_{SS} = -13.5 \text{ V}$
LEAKAGE CURRENTS						$V_{DD} = +16.5 \text{ V}, V_{SS} = -16.5 \text{ V}$
Source OFF Leakage I _S (OFF)	±0.1		±0.1		nA typ	$V_D = \pm 15.5 \text{ V}, V_S = \mp 15.5 \text{ V};$
	±0.25	±5	±0.25	±15	nA max	Test Circuit 2
Drain OFF Leakage I _D (OFF)	±0.1		±0.1		nA typ	$V_D = \pm 15.5 \text{ V}, V_S = \mp 15.5 \text{ V};$
	±0.25	±5	±0.25	±15	nA max	Test Circuit 2
Channel ON Leakage ID, IS (ON)	±0.1		±0.1		nA typ	$V_{\rm S} = V_{\rm D} = \pm 15.5 \text{ V};$
	±0.4	±5	± 0.4	±30	nA max	Test Circuit 3
DIGITAL INPUTS						
Input High Voltage, V _{INH}		2.4		2.4	V min	
Input Low Voltage, V_{INI}		0.8		0.8	V max	
Input Current						
I _{INL} or I _{INH}		±0.005		±0.005	μA typ	$V_{IN} = V_{INI}$ or V_{INH}
INL · INI		±0.5		±0.5	μA max	N IN THE THIRD
DYNAMIC CHARACTERISTICS ²						
t _{ON}	100		100		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$
011	160	200	145	200	ns max	$V_S = \pm 10 \text{ V}$; Test Circuit 4
t_{OFF}	60		60		ns typ	$R_L = 300 \Omega, C_L = 35 pF;$
011	100	150	100	150	ns max	$V_S = \pm 10 \text{ V}$; Test Circuit 4
Charge Injection	7		7		pC typ	$V_S = 0 V, R_L = 0 \Omega,$
,						$C_L = 10 \text{ nF}$; Test Circuit 5
OFF Isolation	80		80		dB typ	$R_L = 50 \Omega$, $f = 1 MHz$;
					31	Test Circuit 6
C_S (OFF)	6		6		pF typ	
C _D (OFF)	6		6		pF typ	
$C_D, C_S (ON)$	55		55		pF typ	
POWER REQUIREMENTS						$V_{DD} = +16.5 \text{ V}, V_{SS} = -16.5 \text{ V}$
I _{DD}	0.0001		0.0001		μA typ	$V_{IN} = 0 \text{ V or 5 V}$
<i>DD</i>	1	2.5	1	2.5	μA max	
I_{SS}	0.0001		0.0001		μA typ	
-00	1	2.5	1	2.5	μA max	
${ m I_L}$	0.0001		0.0001		μA typ	$V_{L} = +5.5 \text{ V}$
-L	1	2.5	1	2.5	μA max	1
NOTES		2.5	*	,	M 1 111111	

NOTES

Specifications subject to change without notice.

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 $^{^1}Temperature$ ranges are as follows: B Version: –40 $^{\circ}C$ to +85 $^{\circ}C;$ T Version: –55 $^{\circ}C$ to +125 $^{\circ}C.$

²Guaranteed by design, not subject to production test.

Single Supply 1 (VDD = +12 V \pm 10%, VSS = 0 V, VL = +5 V \pm 10%, GND = 0 V, unless otherwise noted)

	В	Version -40°C to	T Ve	ersion -55°C to		
Parameter	+25°C	+85°C	+25°C	+125°C	Units	Test Conditions/Comments
ANALOG SWITCH Analog Signal Range R _{ON}	40	0 to V_{DD}	40	0 to V_{DD}	V Ω typ	$V_D = +3 \text{ V}, +8.5 \text{ V}, I_S = -10 \text{ mA}$
		60		70	Ω max	$V_{\rm DD} = +10.8 \text{ V}$
LEAKAGE CURRENT						V _{DD} = +13.2 V
Source OFF Leakage I _S (OFF)	±0.1 ±0.25	±5	±0.1 ±0.25	±15	nA typ nA max	$V_D = 12.2 \text{ V/1 V}, V_S = 1 \text{ V/12.2 V};$ Test Circuit 2
Drain OFF Leakage I_D (OFF)	±0.1		±0.1		nA typ	$V_D = 12.2 \text{ V/1 V}, V_S = 1 \text{ V/12.2 V};$
Channel ON Leakage I_D , I_S (ON)	±0.25 ±0.1 ±0.4	±5 ±5	±0.25 ±0.1 ±0.4	±15 ±30	nA max nA typ nA max	Test Circuit 2 $V_S = V_D = 12.2 \text{ V/1 V};$ Test Circuit 3
DIGITAL INPUTS	20.1		20.1		III III III	rest direction
Input High Voltage, V_{INH} Input Low Voltage, V_{INL}		2.4 0.8		2.4 0.8	V min V max	
Input Current		0.0		0.0	Villux	
I _{INL} or I _{INH}		±0.005 ±0.5		±0.005 ±0.5	μΑ typ μΑ max	$V_{IN} = V_{INL}$ or V_{INH}
DYNAMIC CHARACTERISTICS ²						
t_{ON}	180	250	180	250	ns max	$R_L = 300 \Omega$, $C_L = 35 pF$; $V_S = +8 V$; Test Circuit 4
$t_{ m OFF}$	85	110	85	110	ns max	$R_L = 300 \Omega$, $C_L = 35 pF$; $V_S = +8 V$; Test Circuit 4
Charge Injection	11		11		pC typ	$V_S = 0 \text{ V}, R_S = 0 \Omega,$ $C_L = 10 \text{ nF}; \text{ Test Circuit 5}$
OFF Isolation	80		80		dB typ	$R_L = 50 \Omega$, $f = 1 MHz$; Test Circuit 6
C _s (OFF)	13		13		pF typ	Test Shear 9
C_D (OFF)	13		13		pF typ	
$C_D, C_S (ON)$	65		65		pF typ	
POWER REQUIREMENTS						$V_{\rm DD} = +13.2 \text{ V}$
I_{DD}	0.0001		0.0001		μA typ	$V_{IN} = 0 \text{ V or } 5 \text{ V}$
T	1	2.5	1	2.5	μA max	V - 155V
$ m I_L$	0.0001	2.5	0.0001	2.5	μΑ typ μΑ max	$V_{L} = +5.5 \text{ V}$

NOTES

Specifications subject to change without notice.

Table I. Truth Table

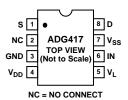
Logic	Switch Condition			
0	ON			
1	OFF			

ORDERING GUIDE

Model	Temperature Range	Package Options*	
ADG417BN	-40°C to +85°C	N-8	
ADG417BR	-40°C to +85°C	SO-8	

^{*}N = Plastic DIP, SO = 0.15" Small Outline IC (SOIC).

PIN CONFIGURATION DIP/SOIC



REV. A -3-

¹Temperature ranges are as follows: B Version: −40 °C to +85 °C; T Version: −55 °C to +125 °C.

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ADG417

ABSOLUTE MAXIMUM RATINGS¹ $(T_A = +25^{\circ}C \text{ unless otherwise noted})$ $m V_{DD}$ to $m V_{SS}$+44 V V_{DD} to GND-0.3 V to +25 V V_{SS} to GND+0.3 V to -25 V or 30 mA, Whichever Occurs First NOTES (Pulsed at 1 ms, 10% Duty Cycle Max) Operating Temperature Range Industrial (B Version)-40°C to +85°C Extended (T Version)-55°C to +125°C Storage Temperature Range-65°C to +150°C Junction Temperature 150°C

Plastic Package, Power Dissipation	400 mW
θ_{IA} , Thermal Impedance	100°C/W
Lead Temperature, Soldering (10 sec)	+260°C
SOIC Package, Power Dissipation	400 mW
θ_{IA} , Thermal Impedance	155°C/W
Lead Temperature, Soldering	
Vapor Phase (60 sec)	+215°C
Infrared (15 sec)	+220°C

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG417 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



"ON." I_L Logic supply current.	TERMINOLOGY V _{DD} V _{SS} V _L GND S D IN R _{ON} I _S (OFF) I _D (OFF) I _D , I _S (ON)	Most positive power supply potential. Most negative power supply potential in dual supplies. In single supply applications, it may be connected to GND. Logic power supply (+5 V). Ground (0 V) reference. Source terminal. May be an input or an output. Drain terminal. May be an input or an output. Logic control input. Ohmic resistance between D and S. Source leakage current with the switch "OFF." Drain leakage current with the switch "OFF." Channel leakage current with the switch	$V_{D} (V_{S})$ $C_{S} (OFF)$ $C_{D} (OFF)$ $C_{D}, C_{S} (ON)$ t_{ON} t_{OFF} V_{INL} V_{INH} $I_{INL} (I_{INH})$ $Charge Injection$ I_{DD} I_{SS}	Analog voltage on terminals D, S. "OFF" switch source capacitance. "OFF" switch drain capacitance. "ON" switch capacitance. Delay between applying the digital control input and the output switching on. Delay between applying the digital control input and the output switching off. Maximum input voltage for logic "0." Minimum input voltage for logic "1." Input current of the digital input. A measure of the glitch impulse transferred from the digital input to the analog output during switching. A measure of unwanted signal coupling through an "OFF" channel. Positive supply current. Negative supply current.
	1D, 18 (O11)	"ON."		

– REV. A

²Overvoltages at IN, S or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

Typical Performance Characteristics—ADG417

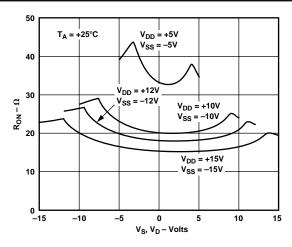


Figure 1. R_{ON} as a Function of V_D (V_S): Dual Supply Voltage

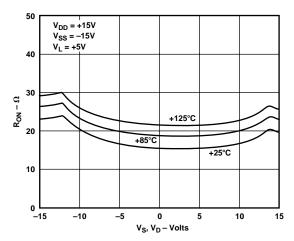


Figure 2. R_{ON} as a Function of V_D (V_S) for Different Temperatures

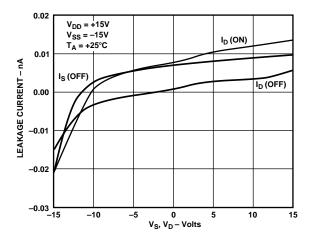


Figure 3. Leakage Currents as a Function of $V_S(V_D)$

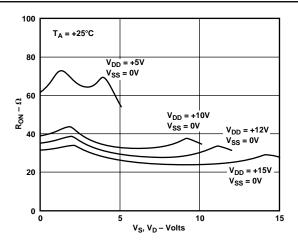


Figure 4. R_{ON} as a Function of V_D (V_S): Single Supply Voltage

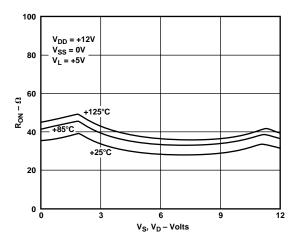


Figure 5. R_{ON} as a Function of V_D (V_S) for Different Temperatures

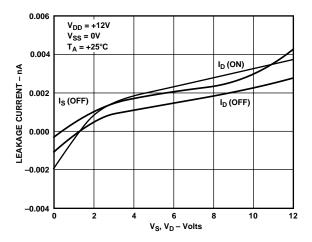


Figure 6. Leakage Currents as a Function of V_S (V_D)

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ADG417

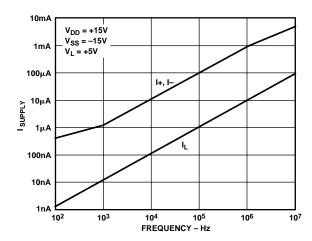


Figure 7. Supply Current vs. Input Switching Frequency

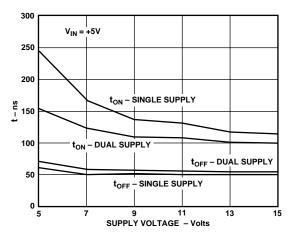
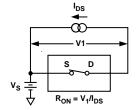


Figure 8. Switching Time vs. Power Supply

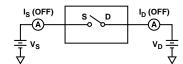
REV. A

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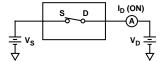
Test Circuits



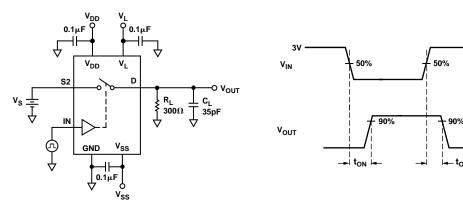
Test Circuit 1. On Resistance



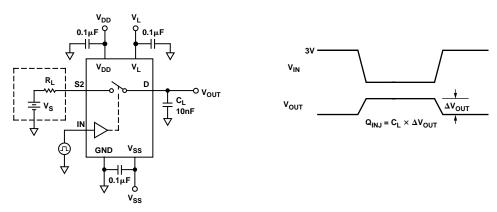
Test Circuit 2. Off Leakage



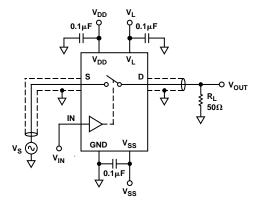
Test Circuit 3. On Leakage



Test Circuit 4. Switching Times



Test Circuit 5. Charge Injection

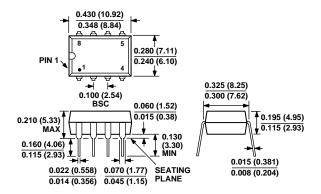


Test Circuit 6. Off Isolation

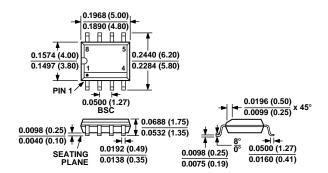
OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

8-Lead Plastic DIP (N-8)



8-Lead SOIC (SO-8) (Narrow Body)



Mouser Electronics

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